Switches and Amplifiers — MOSFET

Ordering Information Preferred Part Number	Package	$V_{GS(th)}$ $V_{GS(off)}$ min/max V		BV_{GSS} min V	I_{DSS} max pA	I_{GSS} max pA	g_{fs} min μmho	$r_{DS(on)}$ max Ω	$I_{D(on)}$ min mA	$I_{Q(on)}$ max mA	
P-Channel Enhancement: Gen. used where max isolation between signal source and logic drive required: sw. "On" resistance varies with signal amplitude.											
3N161	TO-72	-1.5	-5.0	-25	-10 nA	-100.0	3500.0	—	-40	-120	Diode Protected
3N163	TO-72	-2.0	-5.0	-40	-200	-10.0	2000.0	250	- 5	- 30	
3N164	TO-72	-2.0	-5.0	-30	400	10.0	1.0	300	- 3	- 30	
3N172	TO-72	-2.0	-5.0	-40	-400	-10.0	1500.0	250	- 5	- 30	Diode Protected
3N173	TO-72	-2.0	-5.0	-30	-10 nA	-500.0	—	350	- 5	- 30	
IT1700	TO-72	-2.0	-5.0	-40	200	10.0	2.0	400	2	—	
N-Channel Enhancement: Can switch positive signals directly from TTL logic; gen. requires driver or translator circuit to switch bipolar signals.											
2N4351	TO-72	1.0	5.0	25	10 nA	10.0	1000.0	300	3	—	
3N170	TO-72	1.0	2.0	25	10 nA	10.0	1000.0	200	10	—	
3N171	TO-72	1.5	3.0	25	10 nA	10.0	1000.0	200	10	—	
IT1750	TO-72	0.5	3.0	25	10 nA	10.0	30.0	50	10	100	
M116	TO-72	1.0	5.0	30	—	100.0	—	100	—	—	Diode Protected

Special Function

ID-100 ID-101	These products are back to back diode combinations used to protect those P-channel MOSFET duals which are not diode protected. Their chief characteristic is < 1 pA leakage when voltage across them is less than 5 mV. If voltage across diodes is adjusted to 0V ± 0.1 mV, leakage is less than 0.01 pA.
VCR2N VCR3P VCR4N VCR5P VCR7N	The VCR family consists of three terminal variable resistors where the resistance value between two of the terminals is controlled by the voltage potential applied to the third.